Stanislaw Kochowski

List of Publications by Year
in descending order

24	342	1040056 9	794594 19
papers	citations	h-index	g-index

24	24	24	314
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Analysis of MIS equivalent electrical circuit of Au/Pd/Ti-SiO2-GaAs structure based on DLTS measurements. Materials Science-Poland, 2013, 31, 446-453.	1.0	1
2	The analysis of filling pulse parameters influence on ICTS data of GaAs MIS structures. Proceedings of SPIE, 2013, , .	0.8	0
3	Photodeflection signal formation in photothermal measurements: comparison of the complex ray theory, the ray theory, the wave theory, and experimental results. Applied Optics, 2007, 46, 5216.	2.1	10
4	Experimental verification of theory of photodeflection detection based on complex geometrical optics. European Physical Journal Special Topics, 2006, 137, 305-308.	0.2	0
5	Charge transient spectroscopy measurements of GaAs metalâ€“insulatorâ€“semiconductor structures. Applied Surface Science, 2006, 252, 7631-7635.	6.1	0
6	Gaussian optical beam propagation in thermal wave field â€“ the ray theory, the complex ray theory and experimental results. European Physical Journal Special Topics, 2005, 129, 231-236.	0.2	0
7	Characterization of the interface and the bulk phenomena in metalâ€“SiO2â€“(n) GaAs structure by analysis of the equivalent circuit parameters at different temperatures. Thin Solid Films, 2004, 467, 190-196.	1.8	5
8	Studies of GaAs metalâ€“insulatorâ€–semiconductor structures by the admittance spectroscopy method. Applied Surface Science, 2004, 235, 389-394.	6.1	6
9	Two constant phase element behaviour of the admittance characteristics of GaAs metal-insulator-semiconductor structure with deep traps. Thin Solid Films, 2003, 444, 208-214.	1.8	15
10	Bilayer structure for hydrogen detection in a surface acoustic wave sensor system. Sensors and Actuators B: Chemical, 2002, 82, 265-271.	7.8	116
11	Description of the frequency behaviour of metalâ€“SiO2â€–GaAs structure characteristics by electrical equivalent circuit with constant phase element. Thin Solid Films, 2002, 415, 133-137.	1.8	58
12	Some effects of (NH4)2Sx treatment of n-GaAs surface on electrical characteristics of metal-SiO2â€–GaAs structures. Vacuum, 2000, 57, 157-162.	3.5	20
13	Electrical properties of SiO 2 â€“(n) GaAs interface on the basis of measurements of MIS structure capacitance and conductance. Thin Solid Films, 1999, 348, 180-187.	1.8	11
14	An analysis of small-signal response of the SiO2â€–(n) GaAs interface based on a surface disorder model. Vacuum, 1999, 54, 183-188.	3.5	1
15	Electronic properties of the iron phthalocyanine thin films UHV annealed and exposed to oxygen. Vacuum, 1995, 46, 547-549.	3.5	8
16	Photoemission yield spectroscopy investigations of the electronic properties of copper phtalocyanine thin films UHV annealed and exposed to oxygen. Physica Status Solidi (B): Basic Research, 1994, 183, K9.	1.5	6
17	Investigation of sensor properties of copper phthalocyanine with the use of surface acoustic waves. Sensors and Actuators B: Chemical, 1994, 22, 133-137.	7.8	18
18	Electronic properties of the space charge layer of the copper phthalocyanine thin films. European Physical Journal D, 1993, 43, 1041-1044.	0.4	6

#	Article	IF	Citations
19	Description of Electrical Characteristics of Semiconducting Compound-Insulator Interface on the Basis of the Model of Interface States Distributed in Energy and in Space. Acta Physica Polonica A, 1992, 82, 761-764.	0.5	0
20	The contribution of surface effects to the surface photovoltage dependence on temperature for the real Si(111) surface. Surface Science, 1988, 200, 172-178.	1.9	3
21	Investigations by the surface photo-E.M.F. method of the effect of low temperature vacuum baking of an Si(111) surface. Thin Solid Films, 1982, 88, 381-384.	1.8	1
22	Concentration and mobility of charge carriers in thin polycrystalline films of bismuth. Thin Solid Films, 1978, 48, 345-351.	1.8	45
23	An anomalous dependence of the specific resistance on thickness for thin films of Bi in the temperature range 78 â€“ 293 K. Thin Solid Films, 1975, 28, L35-L37.	1.8	1
24	Some electrical properties and structural investigations of thin bismuth films evaporated in a high vacuum. Thin Solid Films, 1973, 17, 199-205.	1.8	11